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REVISION HISTORY

4/08—Rev. 0 to Rev. A

Updated Format.....	Universal
Added Table 6.....	6
Updated Outline Dimensions .....	12
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8/02—Revision 0: Initial Version

## SPECIFICATIONS

$V_{DD} = 5\text{ V} \pm 10\%$ ,  $GND = 0\text{ V}$ ;  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , unless otherwise noted.

Table 1.

Parameter	25°C	−40°C to +85°C	−40°C to +125°C <sup>1</sup>	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>					
Analog Signal Range			0 V to $V_{DD}$	V	
On Resistance ( $R_{ON}$ )	0.5			$\Omega$ typ	$V_S = 0\text{ V}$ to $V_{DD}$ , $I_S = 100\text{ mA}$ , see Figure 17
	0.6	0.7	0.8	$\Omega$ max	
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.16			$\Omega$ typ	$V_S = 0\text{ V}$ to $V_{DD}$ , $I_S = 100\text{ mA}$
	0.2	0.25	0.28	$\Omega$ max	
On Resistance Flatness ( $R_{FLAT(ON)}$ )	0.15			$\Omega$ typ	$V_S = 0\text{ V}$ to $V_{DD}$ , $I_S = 100\text{ mA}$
	0.23	0.26	0.3	$\Omega$ max	
<b>LEAKAGE CURRENTS</b>					
Source Off Leakage, $I_S$ (Off)	$\pm 0.01$			nA typ	$V_{DD} = 5.5\text{ V}$
	$\pm 0.25$	$\pm 3$	$\pm 25$	nA max	$V_S = 4.5\text{ V}/1\text{ V}$ , $V_D = 1\text{ V}/4.5\text{ V}$ , see Figure 18
Drain Off Leakage, $I_D$ (Off)	$\pm 0.01$			nA typ	$V_S = 4.5\text{ V}/1\text{ V}$ , $V_D = 1\text{ V}/4.5\text{ V}$ , see Figure 18
	$\pm 0.25$	$\pm 3$	$\pm 25$	nA max	
Channel On Leakage, $I_D$ , $I_S$ (On)	$\pm 0.01$			nA typ	$V_S = V_D = 1\text{ V}$ , or $V_S = V_D = 4.5\text{ V}$ , see Figure 19
	$\pm 0.25$	$\pm 3$	$\pm 25$	nA max	
<b>DIGITAL INPUTS</b>					
Input High Voltage, $V_{INH}$			2.0	V min	
Input Low Voltage, $V_{INL}$			0.8	V max	
Input Current $I_{INL}$ or $I_{INH}$	0.005			$\mu\text{A}$ typ	$V_{IN} = V_{INL}$ or $V_{INH}$
			$\pm 0.1$	$\mu\text{A}$ max	
Digital Input Capacitance, $C_{IN}$	4			pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>					
$t_{ON}$	33			ns typ	$R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$ , $V_S = 3\text{ V}$ , see Figure 20
	45	48	52	ns max	
$t_{OFF}$	11			ns typ	$R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$ , $V_S = 3\text{ V}$ , see Figure 20
	16	19	21	ns max	
Break-Before-Make Time Delay, $t_{BBM}$ (ADG823 Only)	32		1	ns typ	$R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$ , $V_{S1} = V_{S2} = 3\text{ V}$ , see Figure 21
Charge Injection	15			pC typ	$V_S = 2.5\text{ V}$ ; $R_S = 0\ \Omega$ , $C_L = 1\text{ nF}$ , see Figure 22
Off Isolation	−52			dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ , see Figure 23
Channel-to-Channel Crosstalk	−82			dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ , see Figure 24
Bandwidth −3 dB	24			MHz typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , see Figure 25
$C_S$ (Off)	85			pF typ	$f = 1\text{ MHz}$
$C_D$ (Off)	98			pF typ	$f = 1\text{ MHz}$
$C_D$ , $C_S$ (On)	230			pF typ	$f = 1\text{ MHz}$
<b>POWER REQUIREMENTS</b>					
$I_{DD}$	0.001			$\mu\text{A}$ typ	$V_{DD} = 5.5\text{ V}$ , digital inputs = 0 V or 5.5 V
		1.0	2.0	$\mu\text{A}$ max	

<sup>1</sup> On resistance parameters tested with  $I_S = 10\text{ mA}$ .

<sup>2</sup> Guaranteed by design, not subject to production test.

# ADG821/ADG822/ADG823

$V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$ ,  $GND = 0 \text{ V}$ ,  $T_A = -40^\circ\text{C to } +125^\circ\text{C}$ , unless otherwise noted.

**Table 2.**

Parameter	25°C	−40°C to +85°C	−40°C to +125°C <sup>1</sup>	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>					
Analog Signal Range			0 V to $V_{DD}$	V	
On Resistance ( $R_{ON}$ )	0.7			$\Omega$ typ	$V_S = 0 \text{ V to } V_{DD}$ , $I_S = 100 \text{ mA}$ , see Figure 17
	1.4	1.5	1.6	$\Omega$ max	
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.16			$\Omega$ typ	$V_S = 0 \text{ V to } V_{DD}$ , $I_S = 100 \text{ mA}$
	0.2	0.25	0.28	$\Omega$ max	
On Resistance Flatness ( $R_{FLAT(ON)}$ )	0.3		0.33	$\Omega$ typ	$V_S = 0 \text{ V to } V_{DD}$ , $I_S = 100 \text{ mA}$
<b>LEAKAGE CURRENTS</b>					
Source Off Leakage, $I_S$ (Off)	$\pm 0.01$			nA typ	$V_{DD} = 3.6 \text{ V}$ $V_S = 3.3 \text{ V/1 V}$ , $V_D = 1 \text{ V/3.3 V}$ , see Figure 18
	$\pm 0.25$	$\pm 3$	$\pm 15$	nA max	
Drain Off Leakage, $I_D$ (Off)	$\pm 0.01$			nA typ	$V_S = 3.3 \text{ V/1 V}$ , $V_D = 1 \text{ V/3.3 V}$ , see Figure 18
	$\pm 0.25$	$\pm 3$	$\pm 25$	nA max	
Channel On Leakage, $I_D$ , $I_S$ (On)	$\pm 0.01$			nA typ	$V_S = V_D = 1 \text{ V}$ , or $3.3 \text{ V}$ , see Figure 19
	$\pm 0.25$	$\pm 3$	$\pm 25$	nA max	
<b>DIGITAL INPUTS</b>					
Input High Voltage, $V_{INH}$			2.0	V min	
Input Low Voltage, $V_{INL}$			0.8	V max	
Input Current $I_{INL}$ or $I_{INH}$	0.005		$\pm 0.1$	$\mu\text{A}$ typ $\mu\text{A}$ max	$V_{IN} = V_{INL}$ or $V_{INH}$
Digital Input Capacitance, $C_{IN}$	4			pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>					
$t_{ON}$	48			ns typ	$R_L = 50 \Omega$ , $C_L = 35 \text{ pF}$ , $V_S = 1.5 \text{ V}$ , see Figure 20
	67	74	78	ns max	
$t_{OFF}$	12			ns typ	$R_L = 50 \Omega$ , $C_L = 35 \text{ pF}$ , $V_S = 1.5 \text{ V}$ , see Figure 20
	18	20	23	ns max	
Break-Before-Make Time Delay, $t_{BBM}$ (ADG823 Only)	40		1	ns typ ns min	$R_L = 50 \Omega$ , $C_L = 35 \text{ pF}$ , $V_{S1} = V_{S2} = 1.5 \text{ V}$ , see Figure 21
Charge Injection	$\pm 2$			pC typ	$V_S = 1.5 \text{ V}$ ; $R_S = 0 \Omega$ , $C_L = 1 \text{ nF}$ , see Figure 22
Off Isolation	−52			dB typ	$R_L = 50 \Omega$ , $C_L = 5 \text{ pF}$ , $f = 1 \text{ MHz}$ , see Figure 23
Channel-to-Channel Crosstalk	−82			dB typ	$R_L = 50 \Omega$ , $C_L = 5 \text{ pF}$ , $f = 1 \text{ MHz}$ , see Figure 24
Bandwidth −3 dB	24			MHz typ	$R_L = 50 \Omega$ , $C_L = 5 \text{ pF}$ , see Figure 25
$C_S$ (Off)	85			pF typ	$f = 1 \text{ MHz}$
$C_D$ (Off)	98			pF typ	$f = 1 \text{ MHz}$
$C_D$ , $C_S$ (On)	230			pF typ	$f = 1 \text{ MHz}$
<b>POWER REQUIREMENTS</b>					
$I_{DD}$	0.001			$\mu\text{A}$ typ	$V_{DD} = 3.6 \text{ V}$ , digital inputs = 0 V or 3.6 V
		1.0	2.0	$\mu\text{A}$ max	

<sup>1</sup> On resistance parameters tested with  $I_S = 10 \text{ mA}$ .

<sup>2</sup> Guaranteed by design, not subject to production test.

## ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ , unless otherwise noted.

**Table 3.**

Parameter	Rating
$V_{DD}$ to GND	$-0.3\text{ V to }+7\text{ V}$
Analog Inputs <sup>1</sup>	$-0.3\text{ V to }V_{DD} + 0.3\text{ V}$ or 30 mA, whichever occurs first
Digital Inputs <sup>1</sup>	$-0.3\text{ V to }V_{DD} + 0.3\text{ V}$ or 30 mA, whichever occurs first
Peak Current, S or D	400 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current, S or D	200 mA
Operating Temperature Range	
Automotive	$-40^\circ\text{C to }+125^\circ\text{C}$
Storage Temperature Range	$-65^\circ\text{C to }+150^\circ\text{C}$
Junction Temperature ( $T_J$ max)	$150^\circ\text{C}$
Package Power Dissipation	$(T_J \text{ max} - T_A)/\theta_{JA}$
8-Lead MSOP Thermal Impedance	
$\theta_{JA}$	$206^\circ\text{C/W}$
$\theta_{JC}$	$44^\circ\text{C/W}$
Lead Temperature, Soldering (10 sec)	$300^\circ\text{C}$
IR Reflow, Peak Temperature (<20 sec)	$235^\circ\text{C}$

<sup>1</sup> Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Table 4. Truth Table for the ADG821/ADG822**

ADG821 INx	ADG822 INx	Switch x Condition
0	1	Off
1	0	On

**Table 5. Truth Table for the ADG823**

IN1	IN2	Switch S1	Switch S2
0	0	Off	On
0	1	Off	Off
1	0	On	On
1	1	On	Off

### ESD CAUTION



**ESD (electrostatic discharge) sensitive device.** Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

# ADG821/ADG822/ADG823

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

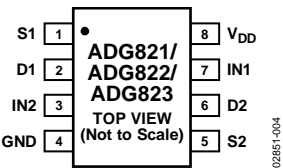


Figure 4. Pin Configuration

Table 6. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	S1	Source Terminal. This pin can be an input or output.
2	D1	Drain Terminal. This pin can be an input or output.
3	IN2	Logic Control Input.
4	GND	Ground (0 V) Reference.
5	S2	Source Terminal. This pin can be an input or output.
6	D2	Drain Terminal. This pin can be an input or output.
7	IN1	Logic Control Input.
8	V <sub>DD</sub>	Most Positive Power Supply Potential.

## TYPICAL PERFORMANCE CHARACTERISTICS

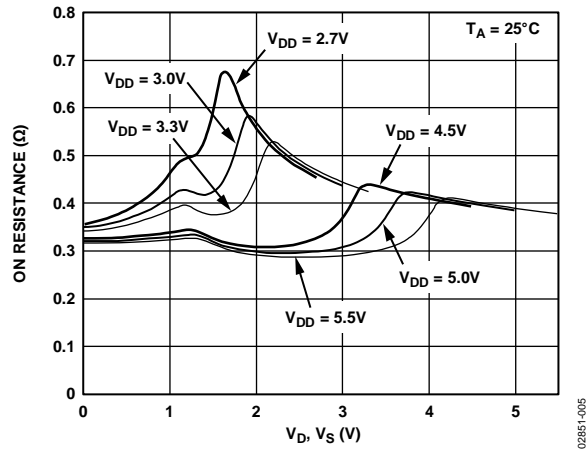


Figure 5. On Resistance vs.  $V_D$ ,  $V_S$

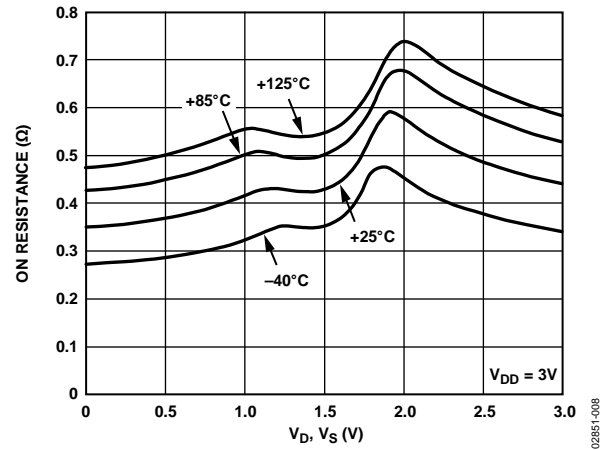


Figure 8. On Resistance vs.  $V_D$ ,  $V_S$  for Different Temperatures,  $V_{DD} = 3V$

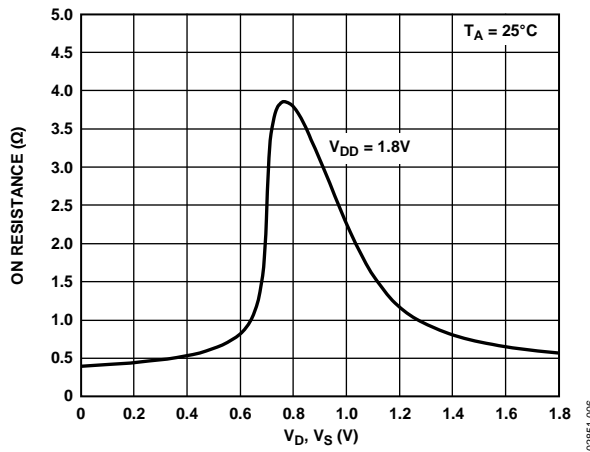


Figure 6. On Resistance vs.  $V_D$ ,  $V_S$ ;  $V_{DD} = 1.8V$

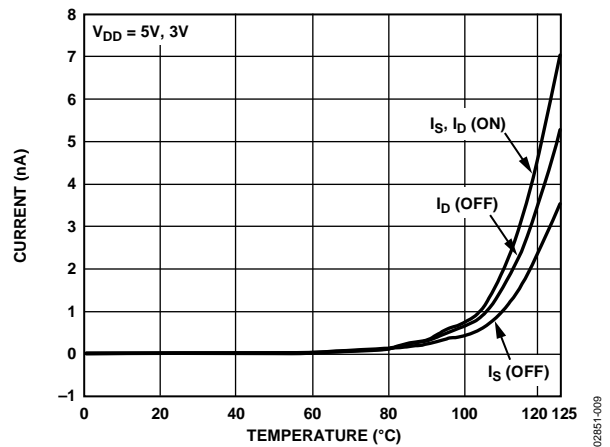


Figure 9. Leakage Current vs. Temperature

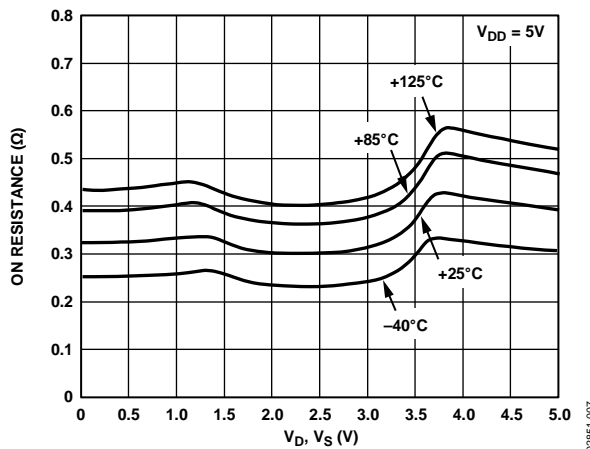


Figure 7. On Resistance vs.  $V_D$ ,  $V_S$  for Different Temperatures,  $V_{DD} = 5V$

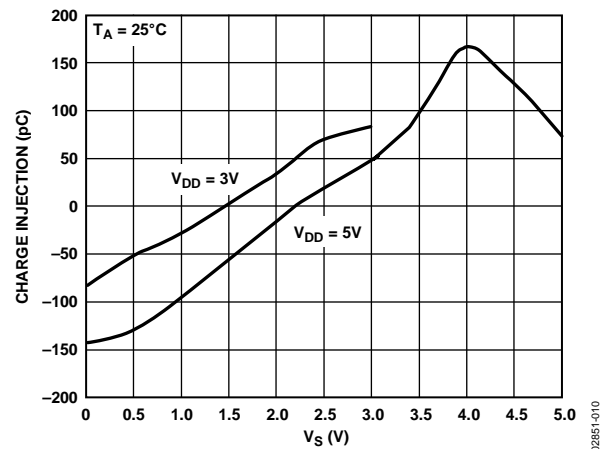


Figure 10. Charge Injection vs. Source Voltage

# ADG821/ADG822/ADG823

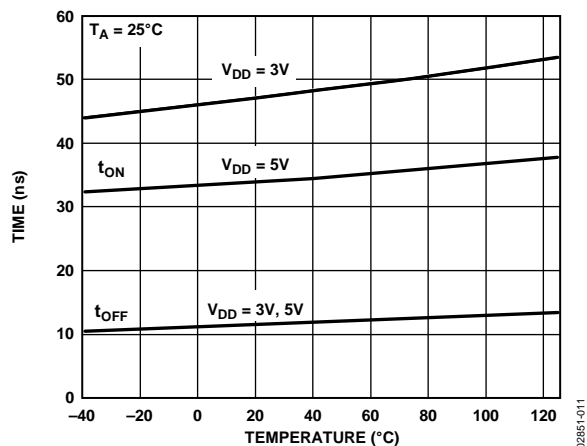


Figure 11.  $t_{ON}/t_{OFF}$  vs. Temperature

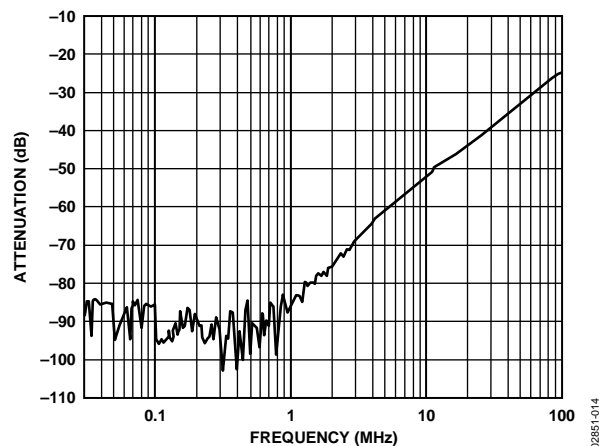


Figure 14. Crosstalk vs. Frequency

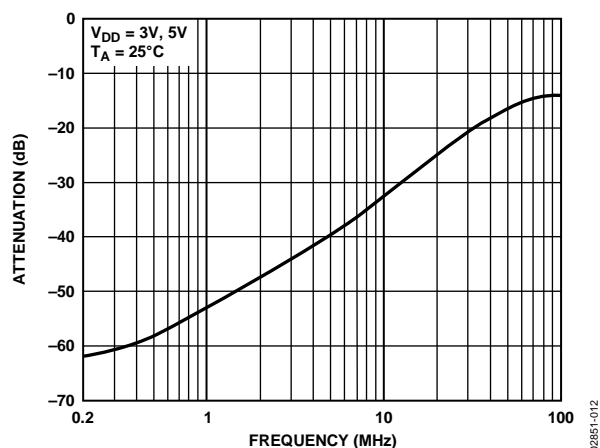


Figure 12. Off Isolation vs. Frequency

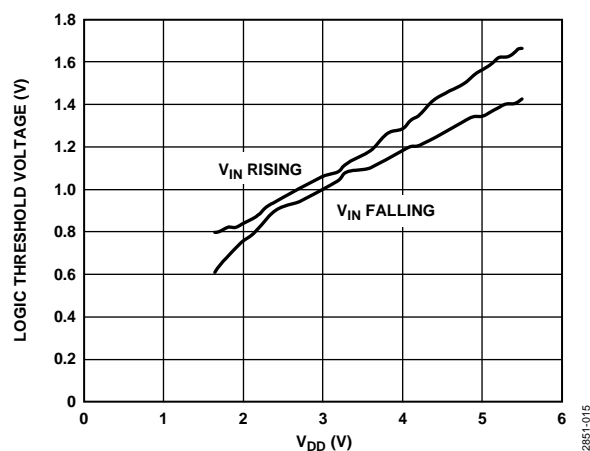


Figure 15. Logic Threshold Voltage vs. Supply Voltage

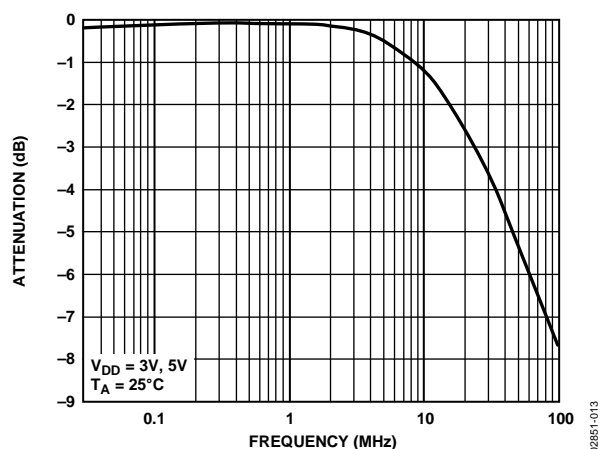


Figure 13. On Response vs. Frequency

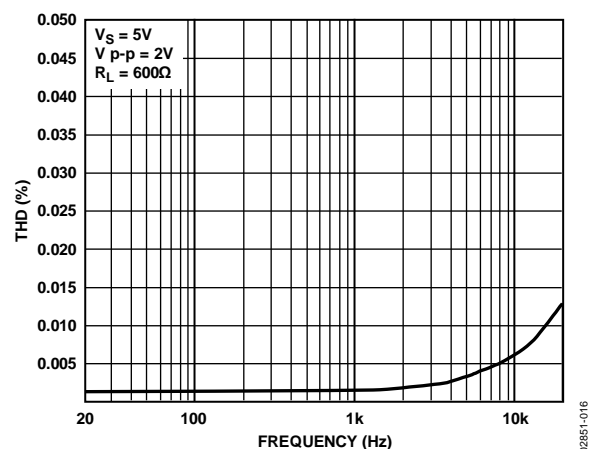


Figure 16. THD vs. Frequency

## TEST CIRCUITS

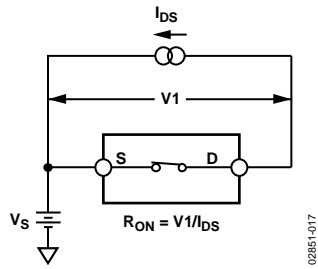


Figure 17. On Resistance

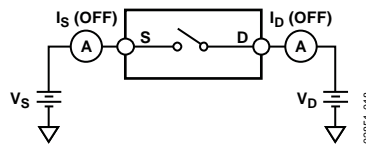


Figure 18. Off Leakage

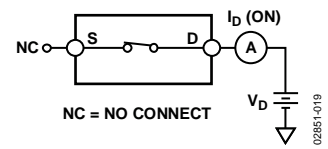


Figure 19. On Leakage

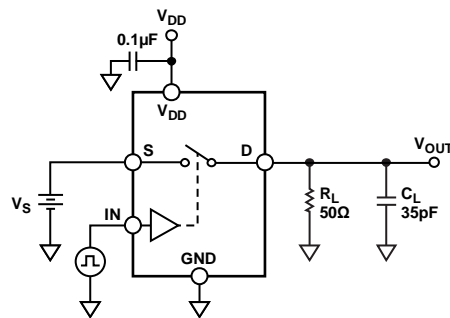


Figure 20. Switching Times

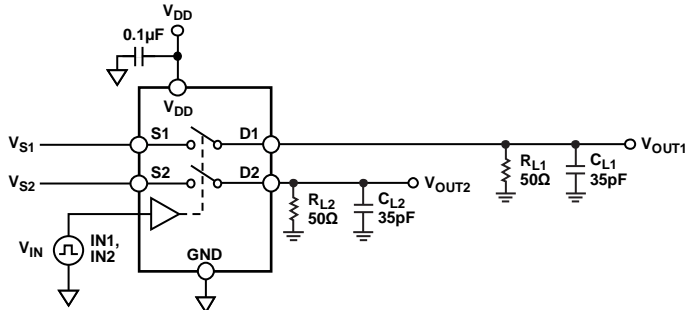
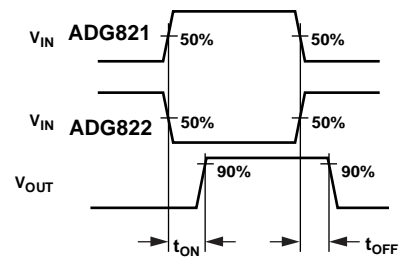


Figure 21. Break-Before-Make Time Delay,  $t_{BBM}$  (ADG823 only)

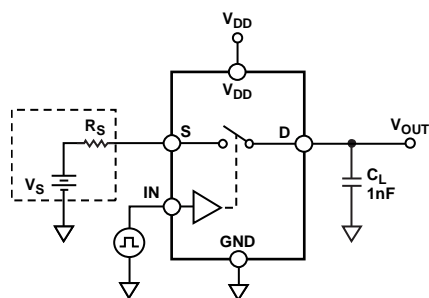
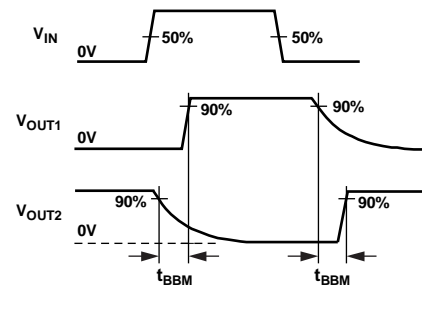
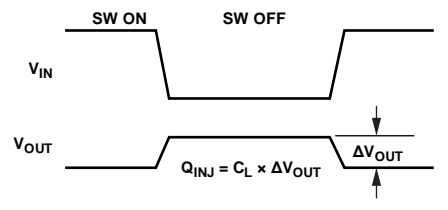


Figure 22. Charge Injection





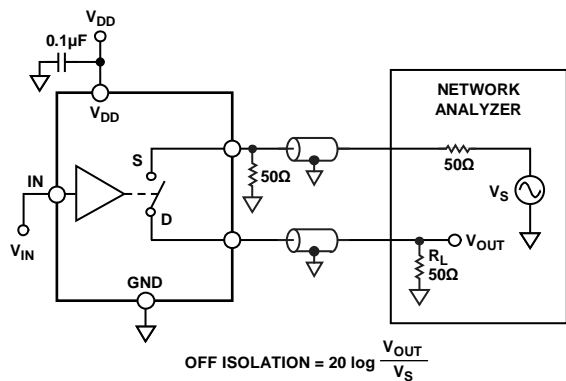


Figure 23. Off Isolation

02851-023

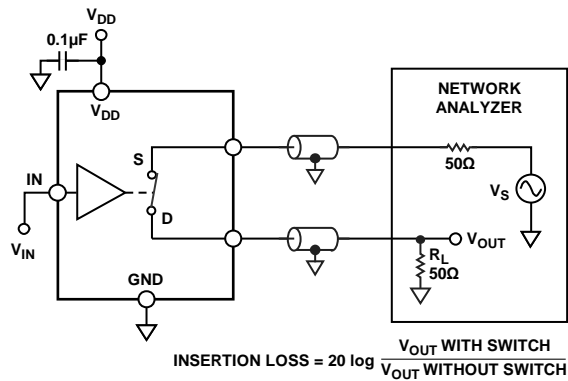


Figure 25. Bandwidth

02851-025

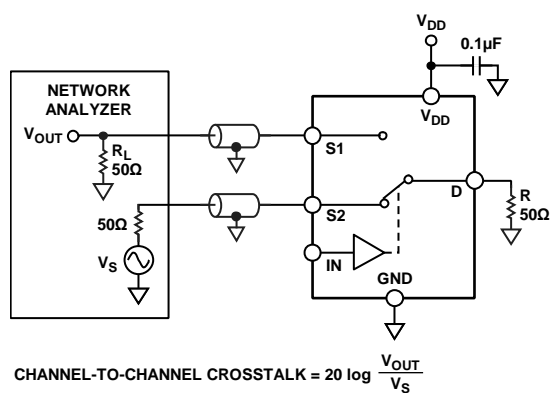


Figure 24. Channel-to-Channel Crosstalk

02851-024

## TERMINOLOGY

**V<sub>DD</sub>**

Most positive power supply potential.

**GND**

Ground (0 V) reference.

**I<sub>DD</sub>**

Positive supply current.

**S**

Source terminal. May be an input or output.

**D**

Drain terminal. May be an input or output.

**IN**

Logic control input.

**R<sub>ON</sub>**

Ohmic resistance between Terminal D and Terminal S.

**ΔR<sub>ON</sub>**

On resistance match between any two channels (that is, R<sub>ON</sub> max – R<sub>ON</sub> min).

**R<sub>FLAT(ON)</sub>**

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

**I<sub>S</sub> (Off)**

Source leakage current with the switch off.

**I<sub>D</sub> (Off)**

Drain leakage current with the switch off.

**I<sub>D</sub>, I<sub>S</sub> (On)**

Channel leakage current with the switch on.

**V<sub>D</sub>, V<sub>S</sub>**

Analog voltage on Terminal D and Terminal S.

**V<sub>INL</sub>**

Maximum input voltage for Logic 0.

**V<sub>INH</sub>**

Minimum input voltage for Logic 1.

**I<sub>INL</sub> (I<sub>INH</sub>)**

Input current of the digital input.

**C<sub>S</sub> (Off)**

Off switch source capacitance.

**C<sub>D</sub> (Off)**

Off switch drain capacitance.

**C<sub>D</sub>, C<sub>S</sub> (On)**

On switch capacitance.

**t<sub>ON</sub>**

Delay between applying the digital control input and the output switching on.

**t<sub>OFF</sub>**

Delay between applying the digital control input and the output switching off.

**t<sub>BBM</sub>**

Off time or on time measured between the 90% points of both switches, when switching from one address state to another.

**Charge Injection**

Charge injection is a measure of the glitch impulse transferred from the digital input to the analog output during switching.

**Crosstalk**

Crosstalk is a measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

**Off Isolation**

A measure of unwanted signal coupling through an off switch.

**Bandwidth**

The frequency at which the output is attenuated by –3 dBs.

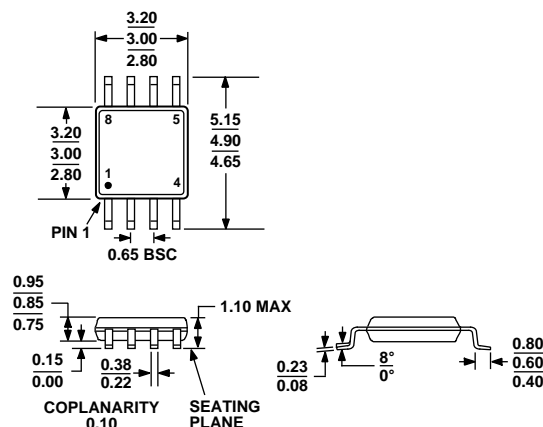
**On Response**

The frequency response of the on switch.

**Insertion Loss**

The loss due to the on resistance of the switch.

## OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-187-AA

Figure 26. 8-Lead Mini Small Outline Package [MSOP]  
(RM-8)  
Dimensions shown in millimeters

## ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding
ADG821BRM	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SQB
ADG821BRM-REEL	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SQB
ADG821BRMZ <sup>1</sup>	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SOP
ADG821BRMZ-REEL <sup>1</sup>	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SOP
ADG822BRM	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SRB
ADG822BRM-REEL	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SRB
ADG822BRM-REEL7	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SRB
ADG822BRMZ <sup>1</sup>	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	S1J
ADG822BRMZ-REEL <sup>1</sup>	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	S1J
ADG823BRM	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SSB
ADG823BRM-REEL	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SSB
ADG823BRMZ <sup>1</sup>	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SSB#
ADG823BRMZ-REEL <sup>1</sup>	−40°C to +125°C	8-Lead Mini Small Outline Package [MSOP]	RM-8	SSB#

<sup>1</sup> Z = RoHS Compliant Part, # denotes RoHS compliant product may be top or bottom marked.